TEXAS INSTRUMENTS

Data sheet acquired from Harris Semiconductor
SCHS196

September 1997

CD74HC688, CD74HCT688

High Speed CMOS Logic 8-Bit Magnitude Comparator

Features

- **Cascadable**
- **Fanout (Over Temperature Range)**
  - **Standard Outputs . . . . . 10 LSTTL Loads**
  - **Bus Driver Outputs . . . . . 15 LSTTL Loads**
- **Wide Operating Temperature Range . . . -55^{O}C to 125^{O}C**
- **Balanced Propagation Delay and Transition Times**
- **Significant Power Reduction Compared to LSTTL Logic ICs**
- **HC Types**
  - **2V to 6V Operation**
  - **High Noise Immunity: N_{IL} = 30%, N_{IH} = 30%of V_{CC} at V_{CC} = 5V**
- **HCT Types**
  - **4.5V to 5.5V Operation**
  - **Direct LSTTL Input Logic Compatibility, V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)**
  - **CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL}, V_{OH}**

Description

The Harris CD74HC688 and CD74HCT688 are 8-bit magnitude comparators designed for use in computer and logic applications that require the comparison of two 8-bit binary words. When the compared words are equal the output (Y) is low and can be used as the enabling input for the next device in a cascaded application.

Ordering Information

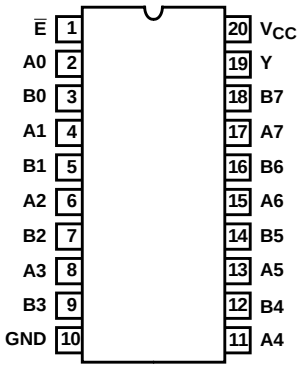
PART NUMBER	TEMP. RANGE (^{O}C)	PACKAGE	PKG. NO.
CD74HC688E	-55 to 125	20 Ld PDIP	E20.3
CD74HCT688E	-55 to 125	20 Ld PDIP	E20.3
CD74HC688M	-55 to 125	20 Ld SOIC	M20.3
CD74HCT688M	-55 to 125	20 Ld SOIC	M20.3
CD54HC688	-55 to 125	Wafer	

NOTES:

1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
2. Die for this part number is available which meets all electrical specifications. Please contact your local sales office or Harris customer service for ordering information.

Pinout

CD74HC688, CD74HCT688
(PDIP, SOIC)
TOP VIEW



CAUTION: These devices are sensitive to electrostatic discharge. Users should follow proper IC Handling Procedures.

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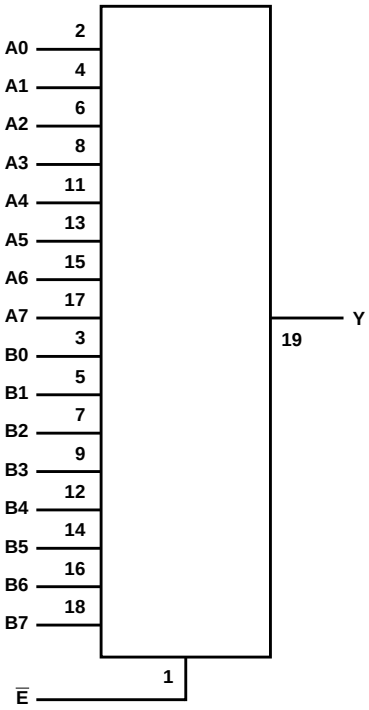
File Number **1646.1**

Functional Diagram

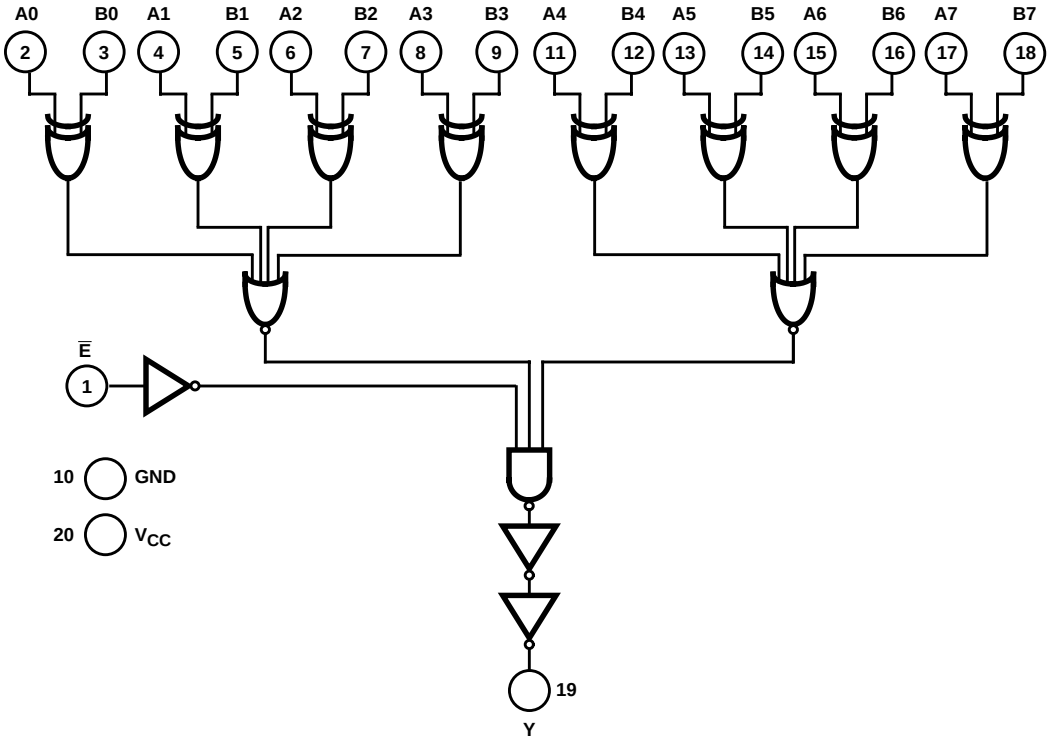


TRUTH TABLE

INPUTS		OUPUTS
A, B	**$\overline{E}$**	**Y**
A = B	L	L
A ≠ B	L	H
X	H	H

NOTES: H = High Voltage Level, L = Low Voltage Level, X = Don't Care

Logic Diagram



Absolute Maximum Ratings

DC Supply Voltage, V_{CC} . . . . . -0.5V to 7V
DC Input Diode Current, I_{IK}
For V_I < -0.5V or V_I > V_{CC} + 0.5V . . . . . ±20mA
DC Output Diode Current, I_{OK}
For V_O < -0.5V or V_O > V_{CC} + 0.5V . . . . . ±20mA
DC Output Source or Sink Current per Output Pin, I_O
For V_O > -0.5V or V_O < V_{CC} + 0.5V . . . . . ±25mA
DC V_{CC} or Ground Current, I_{CC} or I_{GND} . . . . . ±50mA

Operating Conditions

Temperature Range (T_A) . . . . . -55°C to 125°C
Supply Voltage Range, V_{CC}
HC Types . . . . . 2V to 6V
HCT Types . . . . . 4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O . . . . . 0V to V_{CC}
Input Rise and Fall Time
2V . . . . . 1000ns (Max)
4.5V. . . . . 500ns (Max)
6V . . . . . 400ns (Max)

Thermal Information

Thermal Resistance (Typical, Note 3)	θ_{JA} (°C/W)
PDIP Package	125
SOIC Package	100

Maximum Junction Temperature . . . . . 150°C
Maximum Storage Temperature Range . . . . . -65°C to 150°C
Maximum Lead Temperature (Soldering 10s) . . . . . 300°C
(SOIC - Lead Tips Only)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

3. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES												
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V
			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
			-5.2	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V
			4	4.5	-	-	0.26	-	0.33	-	0.4	V
			5.2	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	-	8	-	80	-	160	µA

DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HCT TYPES												
High Level Input Voltage	V_{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V_{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} and GND	0	5.5	-	-	±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	5.5	-	-	8	-	80	-	160	µA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI_{CC} (Note)	V_{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	µA

NOTE: For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
Enable	0.7
Data Inputs	0.35

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Table, e.g., 360µA max at 25°C.

Switching Specifications Input t_r, t_f = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES											
Propagation Delay (Figure 1) An to Output	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	-	170	-	210	-	255	ns
			4.5	-	-	34	-	42	-	51	ns
		C_L =15pF	5	-	14	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	29	-	36	-	43	ns
Bn to Output	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	-	170	-	210	-	255	ns
			4.5	-	-	34	-	42	-	51	ns
		C_L =15pF	5	-	14	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	29	-	36	-	43	ns

Switching Specifications Input t_r, t_f = 6ns **(Continued)**

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
$\overline{E}$ to Output	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	-	120	-	150	-	180	ns
			4.5	-	-	24	-	30	-	36	ns
		C_L =15pF	5	-	9	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	20	-	26	-	30	ns
Output Transition Time (Figure 1)	t_{TLH}, t_{THL}	C_L = 50pF	2	-	-	75	-	95	-	110	ns
			4.5	-	-	15	-	19	-	22	ns
			6	-	-	13	-	16	-	19	ns
Input Capacitance	C_{IN}	C_L = 50pF	-	-	-	10	-	10	-	10	pF
Power Dissipation Capacitance (Notes 4, 5)	C_{PD}	C_L =15pF	5	-	22	-	-	-	-	-	pF
HCT TYPES											
Propagation Delay (Figure 1)	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	-	34	-	42	-	51	ns
An to Output		C_L =15pF	5	-	14	-	-	-	-	-	ns
Bn to Output	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	-	34	-	42	-	51	ns
		C_L =15pF	5	-	14	-	-	-	-	-	ns
$\overline{E}$ to Output	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	-	24	-	30	-	36	ns
		C_L =15pF	5	-	9	-	-	-	-	-	ns
Output Transition Time (Figure 1)	t_{TLH}, t_{THL}	C_L = 50pF	4.5	-	-	15	-	19	-	22	ns
Input Capacitance	C_{IN}	C_L = 50pF	-	-	-	10	-	10	-	10	pF
Power Dissipation Capacitance (Notes 4, 5)	C_{PD}	C_L =15pF	5	-	22	-	-	-	-	-	pF

NOTES:

4. C_{PD} is used to determine the dynamic power consumption, per gate.
5. $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = Input Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuit and Waveform

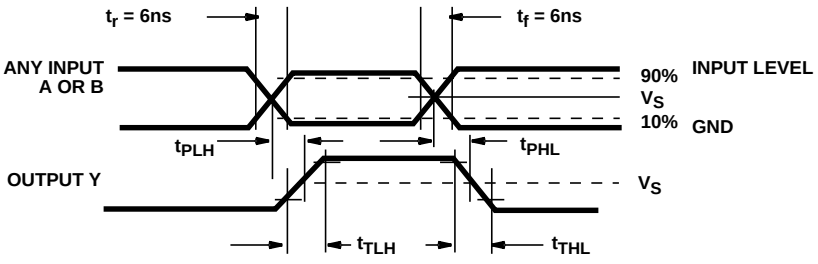


FIGURE 1. PROPAGATION DELAY AMD TRANSITION TIMES

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